

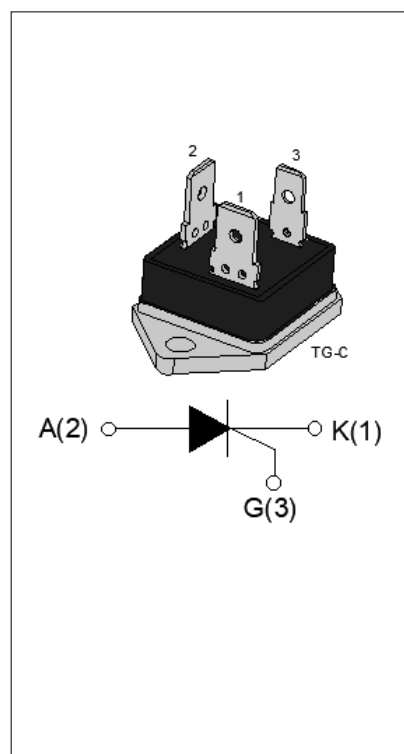


DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT1675T SCR provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, UPS, SVC, power charger, T-tools etc. complying with UL standards (File ref: E252906). Package TG-C is RoHS compliant.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	75	A
V_{DRM}/V_{RRM}	1600	V
I_{GT}	10-80	mA



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	1600	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	1600	V
Average on-state current ($T_c \leq 68^\circ\text{C}$)	$I_{T(AV)}$	48	A
RMS on-state current ($T_c \leq 68^\circ\text{C}$)	$I_{T(RMS)}$	75	A
Non repetitive surge peak on-state current ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	700	A
Non repetitive surge peak on-state current ($t_p=8.3\text{ms}$, $T_j=25^\circ\text{C}$)		750	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	2450	A^2s
Critical rate of rise of on-state current ($I_G=2 I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	di/dt	200	$\text{A}/\mu\text{s}$

Peak gate current ($t_p=20\mu s$, $T_j=125$)	I_{GM}	12	A
Average gate power dissipation ($T_j=125$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	22	W
Peak pulse voltage ($T_j=25$; non-repetitive,off-state;FIG.7)	V_{pp}	1	kV

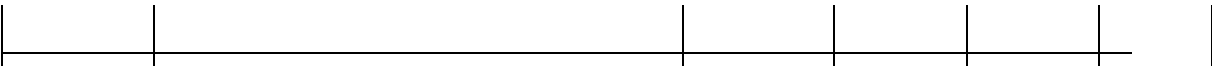
ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12V$ $R_L=33\Omega$	10	-	80	mA
V_{GT}		-	-	1.3	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3k\Omega$	0.25	-	-	V
I_L	$I_G=1.2I_{GT}$	-	-	250	mA
I_H	$I_T=500mA$	-	-	200	mA
dV/dt	$V_D=1070V$ Gate Open $T_j=125$	2000	-	-	V/ μs

t_{on} I

=10mA

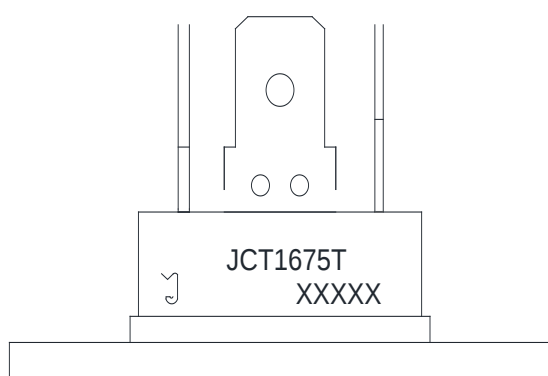
=100mA



ORDERING INFORMATION

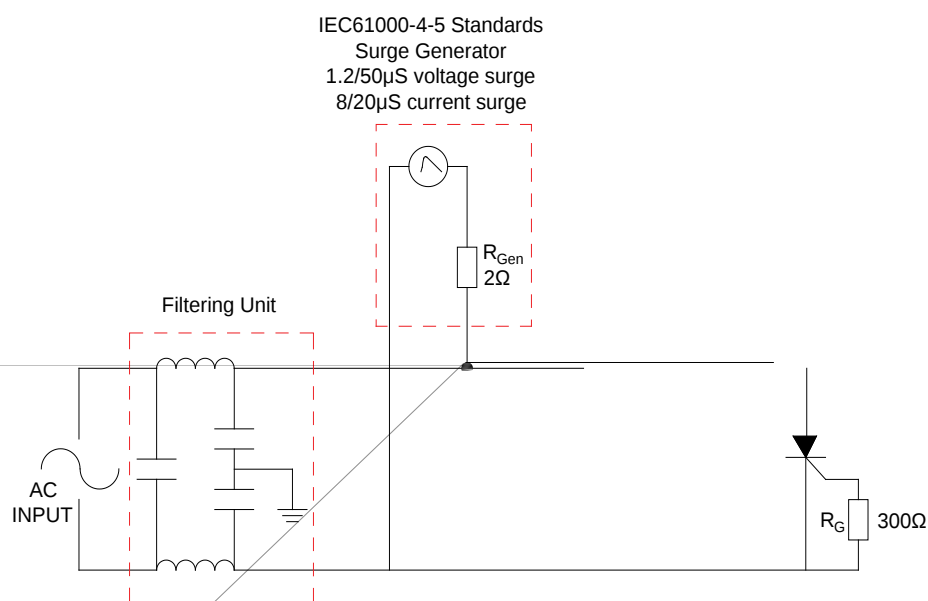
<u>J</u>	<u>CT</u>	<u>16</u>	<u>75</u>	<u>T</u>
JieJie Microelectronics Co., Ltd.	SCRs	16:V _{DRM} /V _{RRM} •1600V	I _{T(RMS)} :75A	T:TG-C

MARKING



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FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



ORDERING INFORMATION

Order code	Voltage $V_{\text{DRM}}/V_{\text{RRM}}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT1675T	1600	10-80	TG-C	10	Tube

Document Revision History

Date	Revision	Changes
Apr.13, 2023	A.1.0	Last update

PACKAGE MECHANICAL DATA



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